

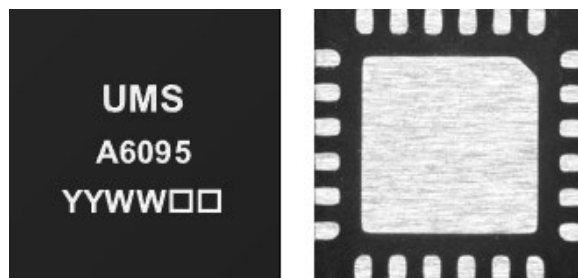
35-42.5GHz 4W Packaged Power Amplifier

GaN Monolithic Microwave IC in SMD leadless package

Description

The CHA6095-QKB is a GaN packaged Power Amplifier operating over 35-42.5GHz frequency band. It typically exhibits 36dBm saturated output power with 25dB small signal gain. For 256QAM modulation signal & 120MHz channel spacing the linear power is 31dBm with ACPR below -30dBc and it is 29dBm with EVM below 3.5%.

The CHA6095-QKB is designed for telecom applications such as 5G active phased array antennas, Satcom and Radar systems. It is manufactured on a robust GaN-on-SiC HEMT technology and packaged in a standard surface mount 4x4 plastic QFN which is RoHS compliant. RF input and output are 50Ω matched and integrate ESD RF protections.

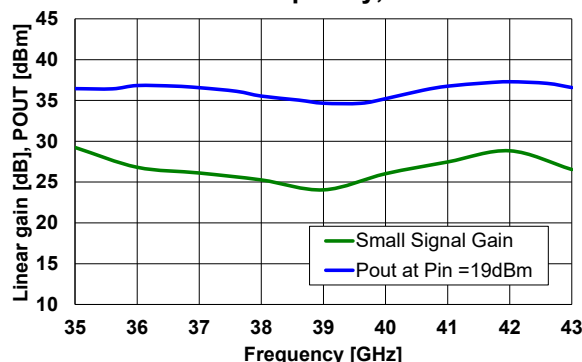


Main Features

- Frequency range: 35-42.5GHz
- Pout = 36dBm @ 20dBm input power
- Linear Gain = 25dB
- ACPR < -30dBc at 31dBm Average Pout⁽¹⁾
- EVM < 3.5% at 29dBm Average Pout⁽¹⁾
- DC bias: Vd=25V @ Idq=300mA
- 24L-QFN RoHS plastic package 4x4mm²
- MSL3

⁽¹⁾ 120MHz modulation bandwidth, 256QAM

Small Signal Gain & Output Power at Pin = 20dBm vs. Frequency, T° = 25°C



Main Electrical Characteristics

Tcase = +25°C (Tcase: QFN backside temperature)

Symbol	Parameter	Min	Typ	Max	Unit
Freq	Frequency range	35.0		42.5	GHz
Gain	Linear Gain		25		dB
ACPR	ACPR @ P _{AVG} = 27dBm with 256QAM & 120MHz modulation bandwidth		-33		dBc
P _{MAX}	Maximum Output Power at PAE _{MAX}		36		dBm

Specifications

Tcase = +25°C, Vd = +25V (QFN reference plans)

Symbol	Parameter	Min	Typ	Max	Unit
Freq	Frequency range	35.0		42.5	GHz
Gain	Linear Gain		25		dB
IRL ^(*)	Input Return Losses		10		dB
ORL ^(*)	Output Return Losses		10		dB
PAE _{MAX}	Maximum Power Added Efficiency		12		%
P _{MAX}	Output Power at PAE _{MAX}		36		dBm
ACPR	Transmit ACPR@ P _{AVG} =27dBm, 256QAM 120MHz modulation bandwidth		-33		dBc
EVM	Transmit EVM @ P _{AVG} =27dBm for 256QAM, 120MHz modulation bandwidth		-31		dB
Vd	CW Drain Voltage		25		V
Vg	CW Gate Voltage		-2.9		V
Idq	Quiescent Drain bias current		300		mA

These values are representative of measurements performed on evaluation board - see paragraph "Evaluation board".

(*) Input and Output Return Loss are given at RF reference plan of Evaluation board (see Definition of the board reference planes section).

Absolute Maximum Ratings ⁽¹⁾T_{case} = +25°C

Symbol	Parameter	Values	Unit
V _d	Drain bias voltage	27	V
I _{dq}	Quiescent Drain bias current	400	mA
V _g	Gate bias voltage	-7 to -2	V
P _{in}	Maximum Input Power	23	dBm

⁽¹⁾ Operation of this device above any of these parameters may cause permanent damage.**Recommended Operating Range ^{(2), (3)}**

Symbol	Parameter	Values	Unit
V _d	Drain bias voltage	20 to 25	V
I _d	Quiescent Drain bias current	140 to 300	mA
V _g	Gate bias voltage	-5 to -2.8	V
P _{in}	Maximum Input Power	21	dBm
T _j	Maximum Junction temperature ⁽⁴⁾	200	°C

⁽²⁾ Electrical performances are defined for specified test conditions⁽³⁾ Electrical performances are not guaranteed over all recommended operating conditions⁽⁴⁾ See Device thermal performances section**Temperature Range**

T _{case}	Operating temperature range	-40 to +85	°C
T _{stg}	Storage temperature range	-55 to +150	°C

Typical Bias ConditionsT_{case}=+25°C

Symbol	Pad N°	Parameter	Values	Unit
VG12N	1	North 1 st Gate bias voltage	-2.9	V
VG3N	23	North 2 nd Gate bias voltage	-2.9	V
VG4N	22	North 3 th Gate bias voltage	-2.9	V
VD12N	21	North 1 st Drain bias voltage	25	V
VD3N	20	North 2 nd Drain bias voltage	25	V
VD4N	18	North 3 th Drain bias voltage	25	V
VG12S	7	South 1 st Gate bias voltage	-2.9	V
VG3S	8	South 2 nd Gate bias voltage	-2.9	V
VG4S	9	South 3 th Gate bias voltage	-2.9	V
VD12S	10	South 1 st Drain bias voltage	25	V
VD3S	11	South 2 nd Drain bias voltage	25	V
VD4S	12	South 3 th Drain bias voltage	25	V

“Power ON” sequence

1. Bias HPA gate voltage V_g (VG12N, VG3N, VG4N, VG12S, VG3S, VG4S) close to $V_{pinch-off}$ (Typically: $V_g \approx -5V$)
2. Apply drain bias voltage V_d (VD12N, VD3N, VD4N, VD12S, VD3S, VD4S) (Typically: $V_d = 25V$)
3. Increase gate voltage V_g (VG12N, VG3N, VG4N, VG12S, VG3S, VG4S) up to quiescent bias drain current I_{dq}
4. Apply RF signal

“Power OFF” sequence

1. Turn off RF signal
2. Bias HPA gate voltage V_g (VG12N, VG3N, VG4N, VG12S, VG3S, VG4S) close to $V_{pinch-off}$ (Typically: $V_g \approx -5V$)
3. Check that quiescent bias drain current I_{dq} is close to 0mA
4. Turn drain bias voltage V_d (VD12N, VD3N, VD4N, VD12S, VD3S, VD4S) to 0V
5. Check that quiescent bias drain current I_{dq} is close to 0mA
6. Turn gate voltage V_g (VG12N, VG3N, VG4N, VG12S, VG3S, VG4S) to 0V

Device thermal performances

All figures given in this section are obtained assuming the QFN device is only cooled down by conduction through the package thermal pad (no convection mode is considered).

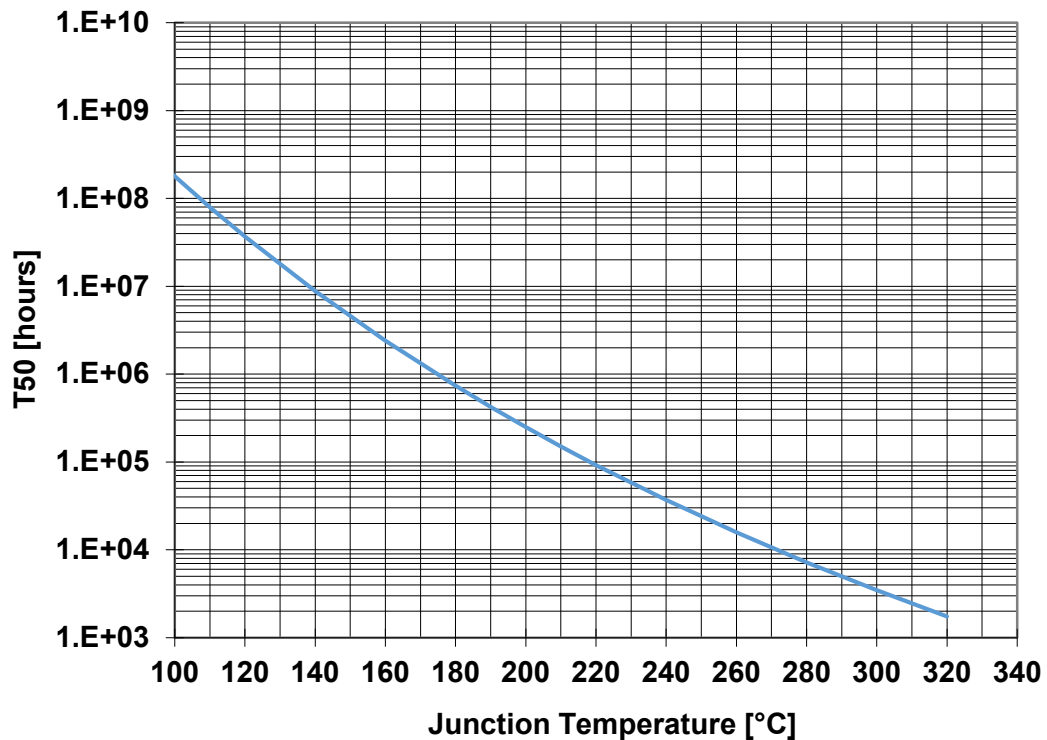
The temperature is monitored at the package back-side interface (Tcase).

The system maximum temperature must be adjusted in order to guarantee that Tjunction remains below the maximum value specified in the Recommended Operating Range table.

The system PCB must be designed to comply with this requirement

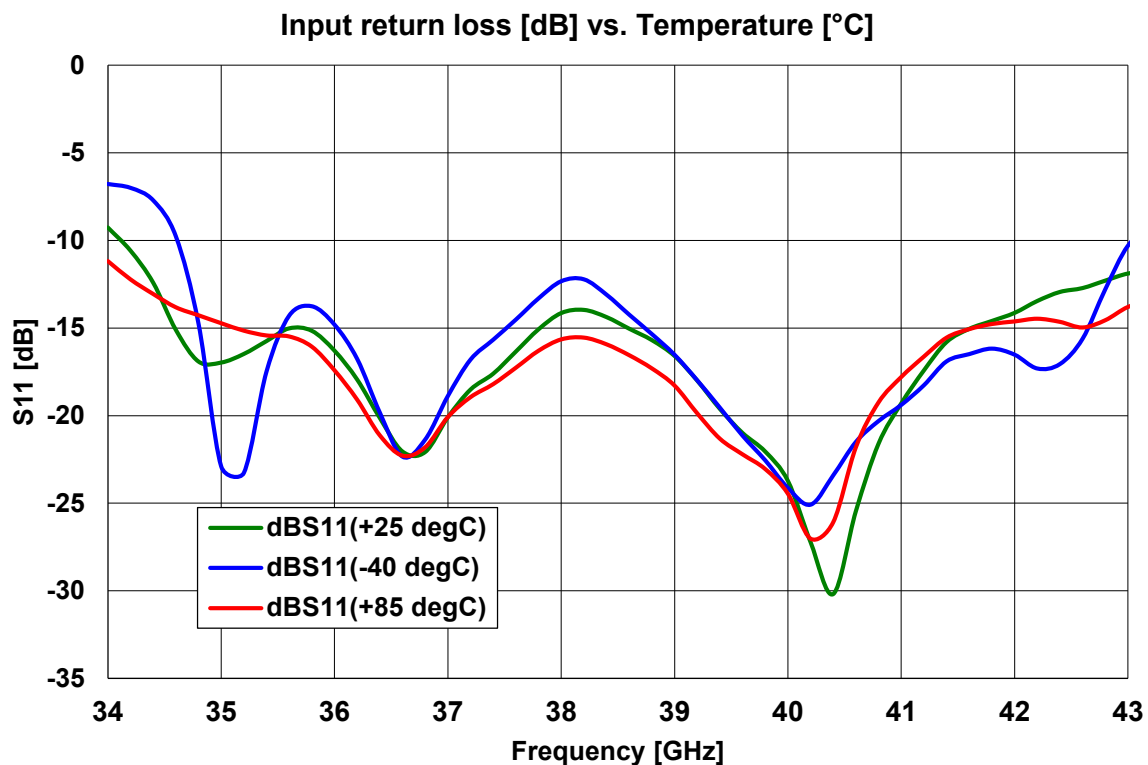
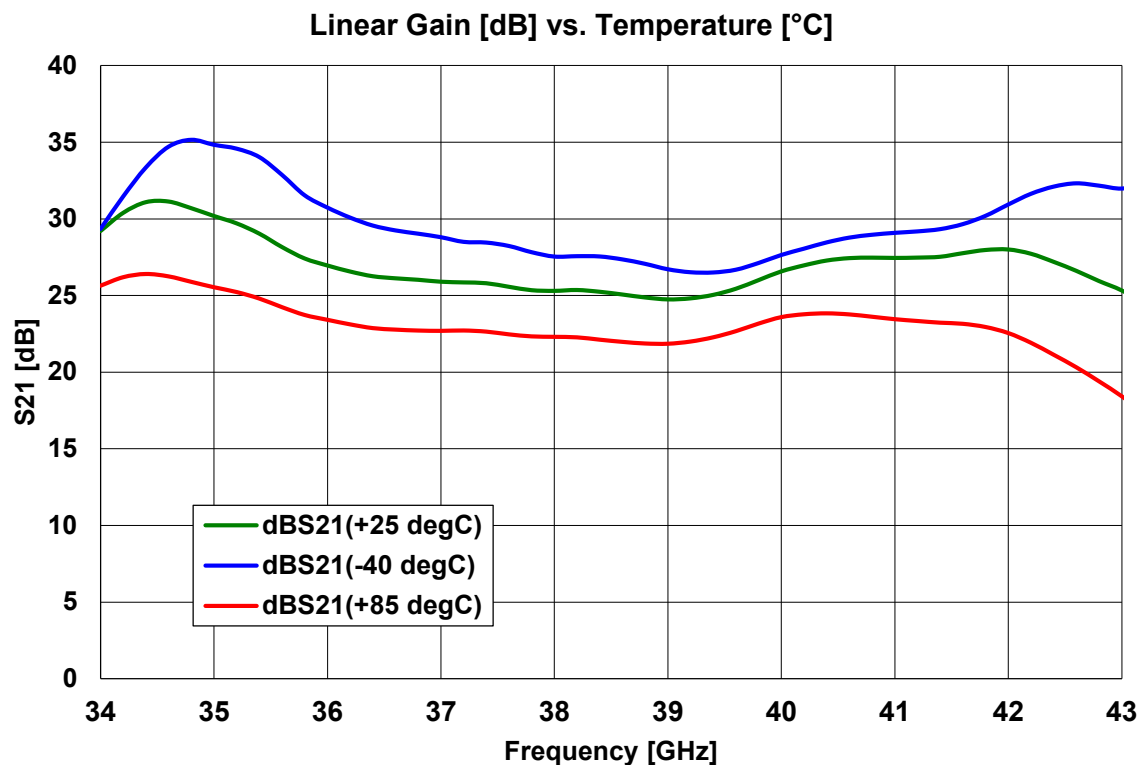
Parameter	DC & RF conditions	Tjunction (°C)	R _{TH} (°C/W)	T50 (hours)
R _{TH} ⁽¹⁾ Thermal Resistance (Junction to Case)	Vd= 25V Id= 300mA Pout= 26dBm Pdiss= 12.7W	137	4.1	8.8E+06
	Vd= 25V Id= 300mA Pout= 33dBm Pdiss= 21.7W	200	5.3	2.5E+05

⁽¹⁾ Assuming 85°C Tcase



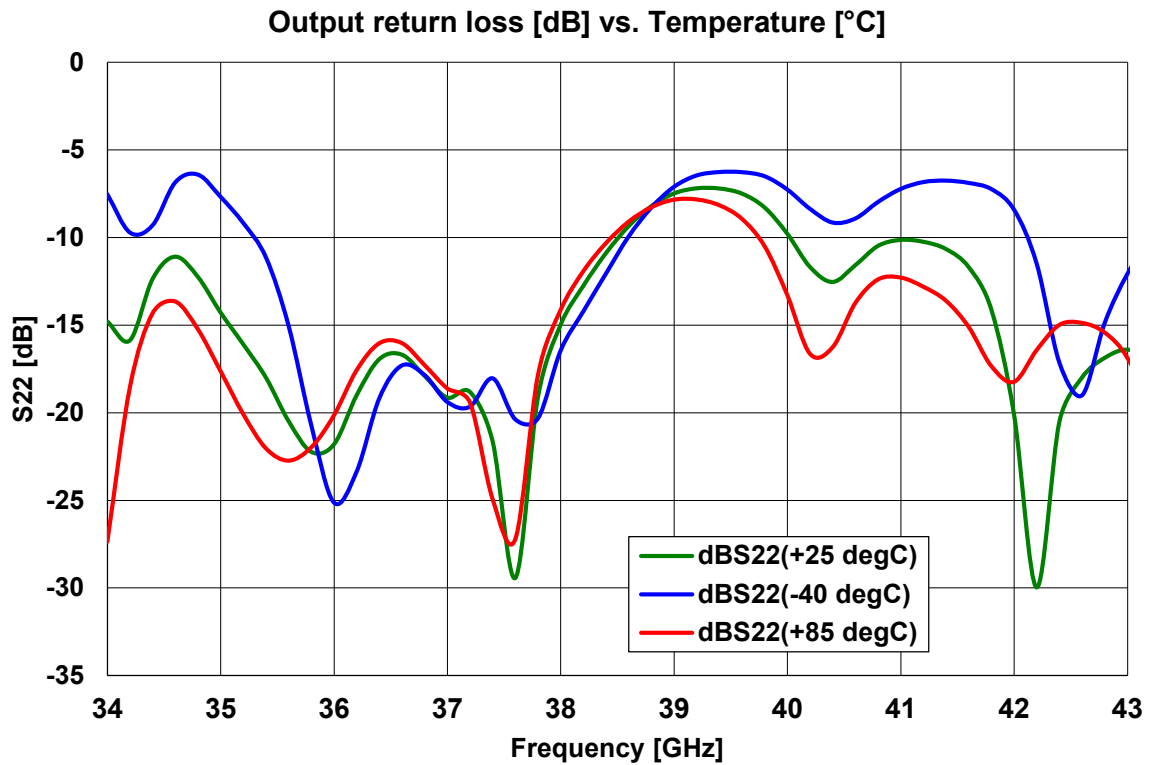
Typical on board Measurements: Small signal performance

Tcase=-40°C/+25°C/+85°C (QFN backside), Vd = +25V, Idq = 300mA



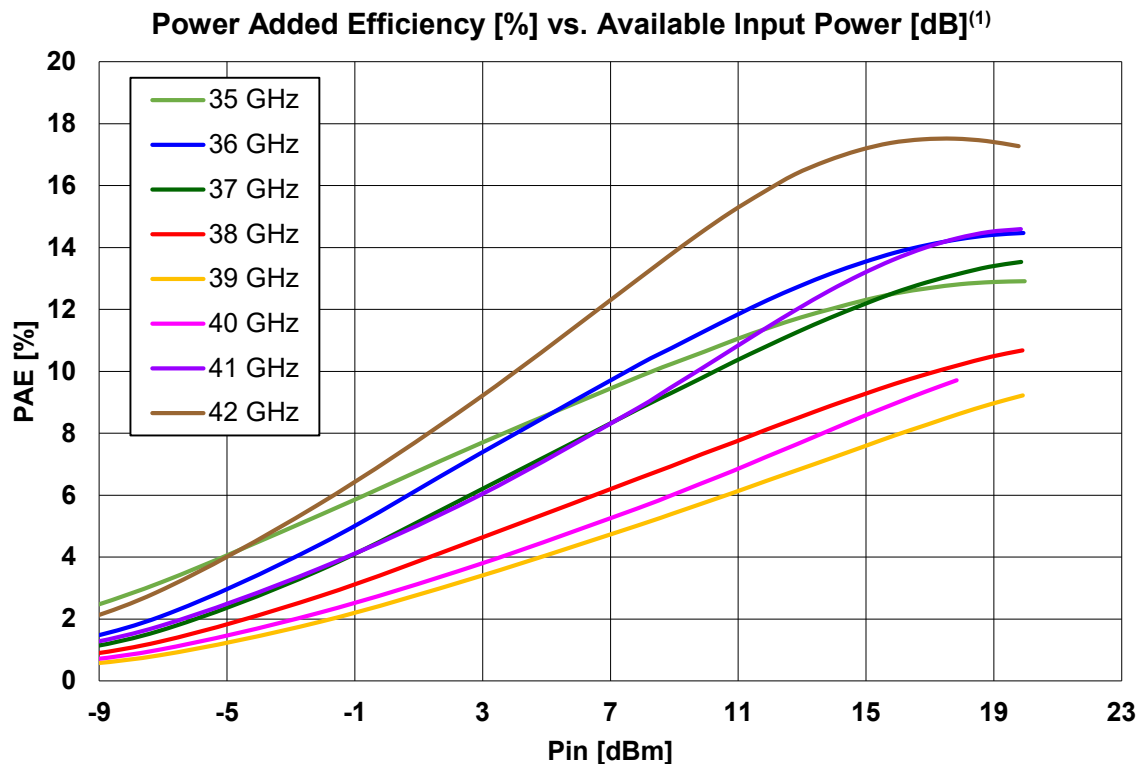
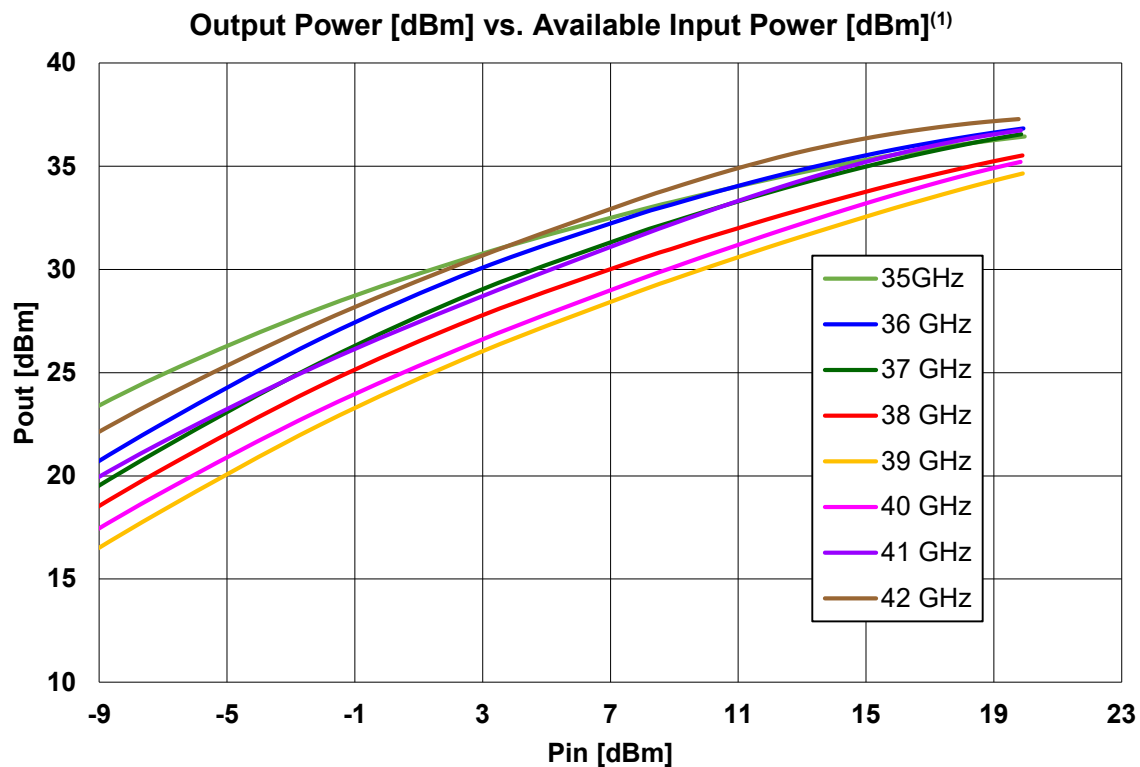
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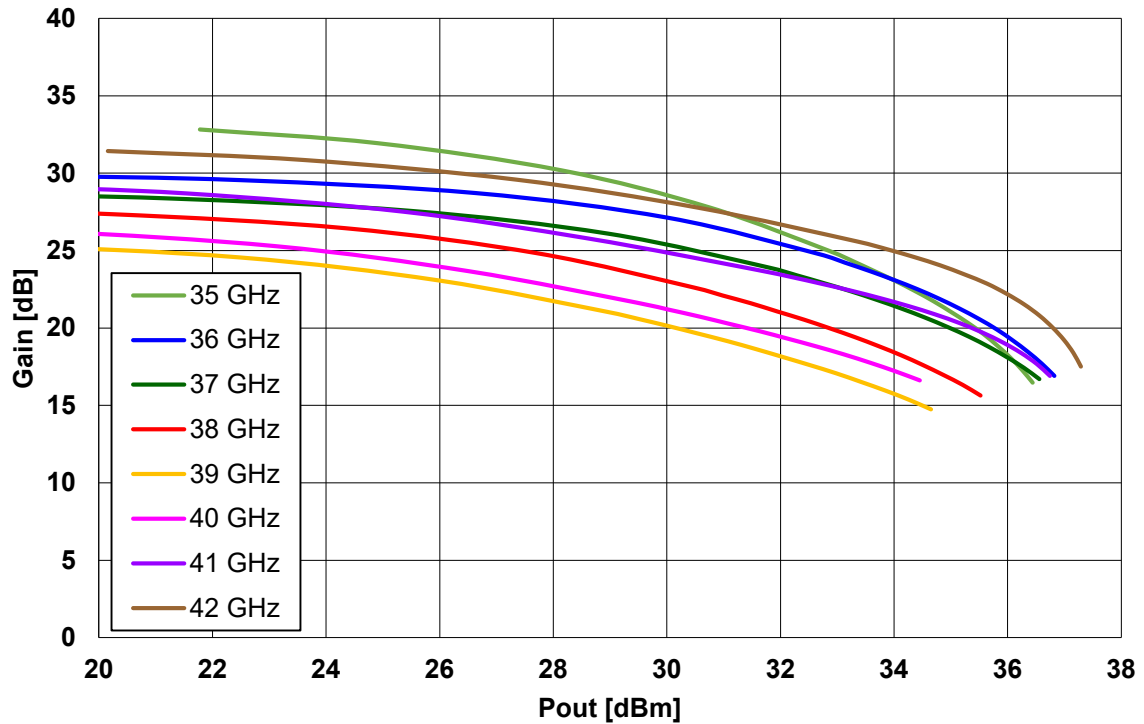
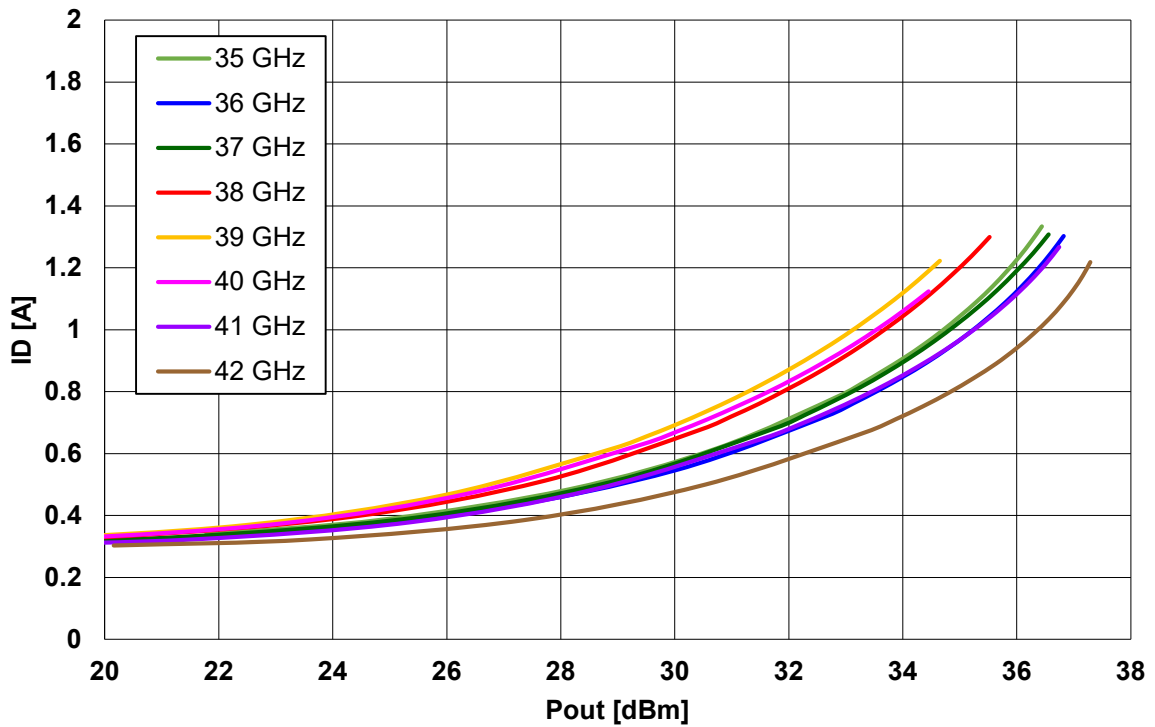
Tcase=+25°C (QFN backside), Vd = +25V, Idq = 300mA



⁽¹⁾ The temperature is fixed at Tcase = 25°C with Pout = 36dBm.

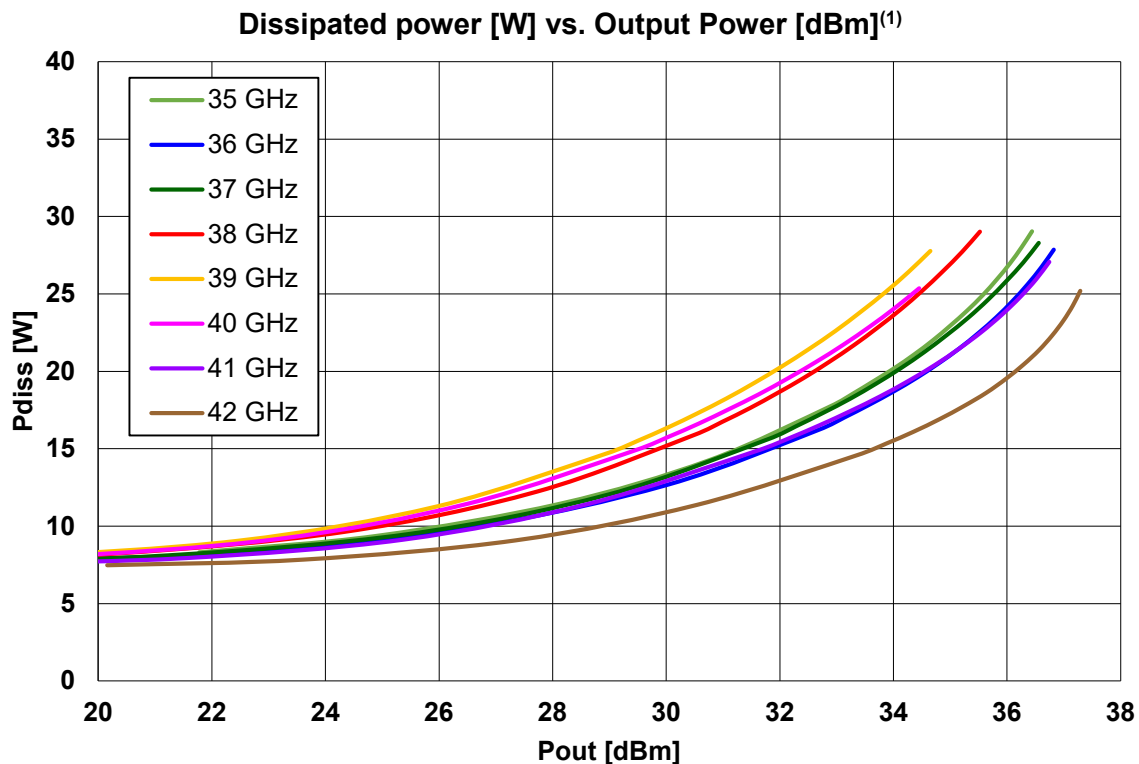
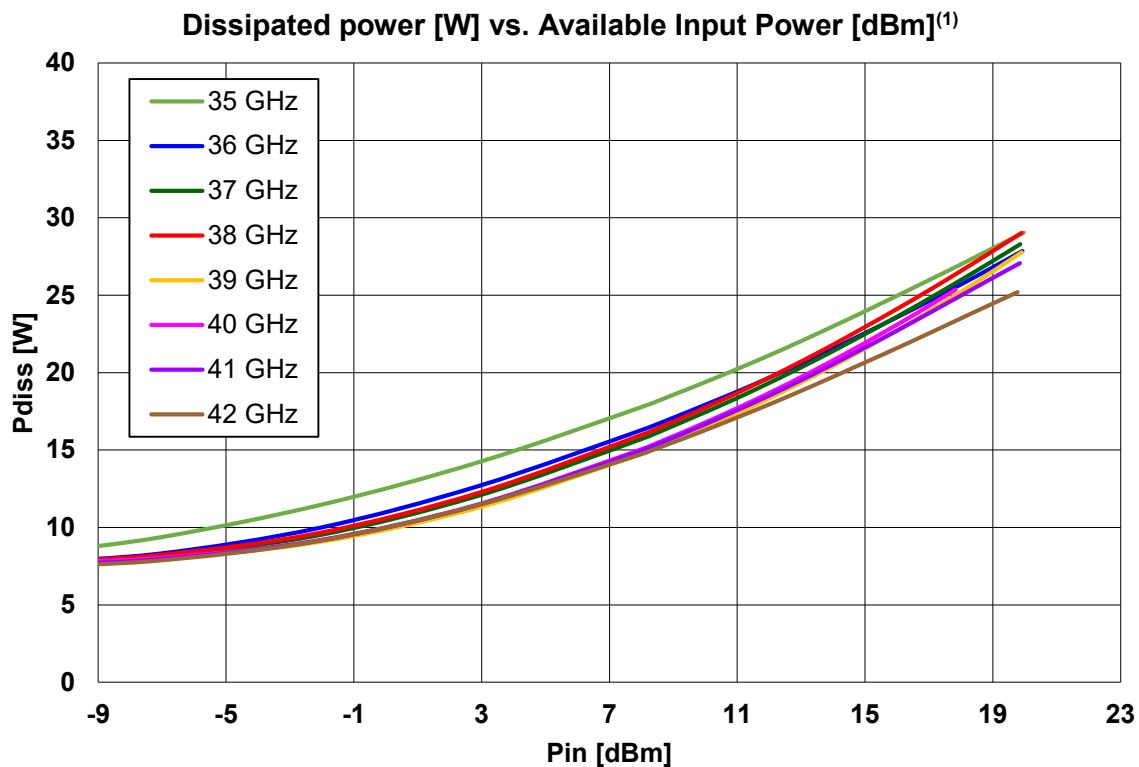
Typical on board Measurements: Large signal performance

Tcase=+25°C (QFN backside), Vd = +25V, Idq = 300mA

Gain [dB] vs. Output Power [dBm]⁽¹⁾**Drain current [A] vs. Output Power [dBm]⁽¹⁾**⁽¹⁾ The temperature is fixed at Tcase = 25°C with Pout = 36dBm.

Typical on board Measurements: Large signal performance

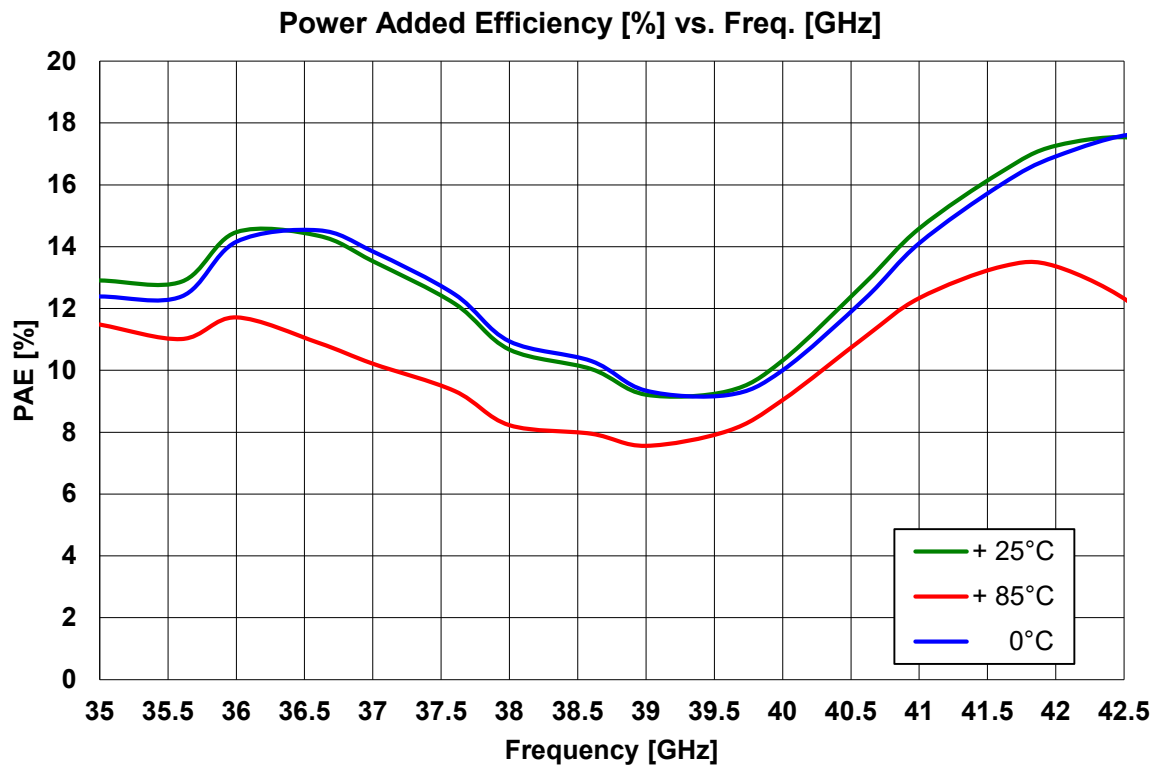
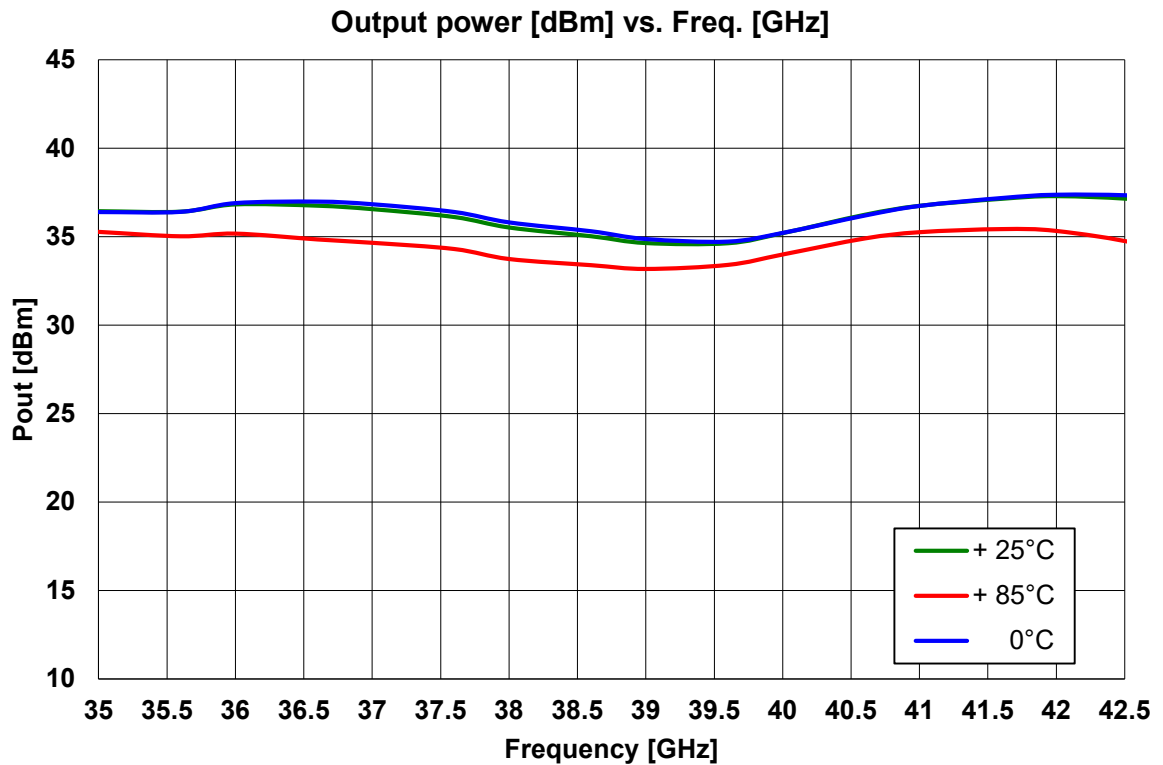
Tcase=+25°C (QFN backside), Vd = +25V, Idq = 300mA



⁽¹⁾ The temperature is fixed at Tcase = 25°C with Pout = 36dBm.

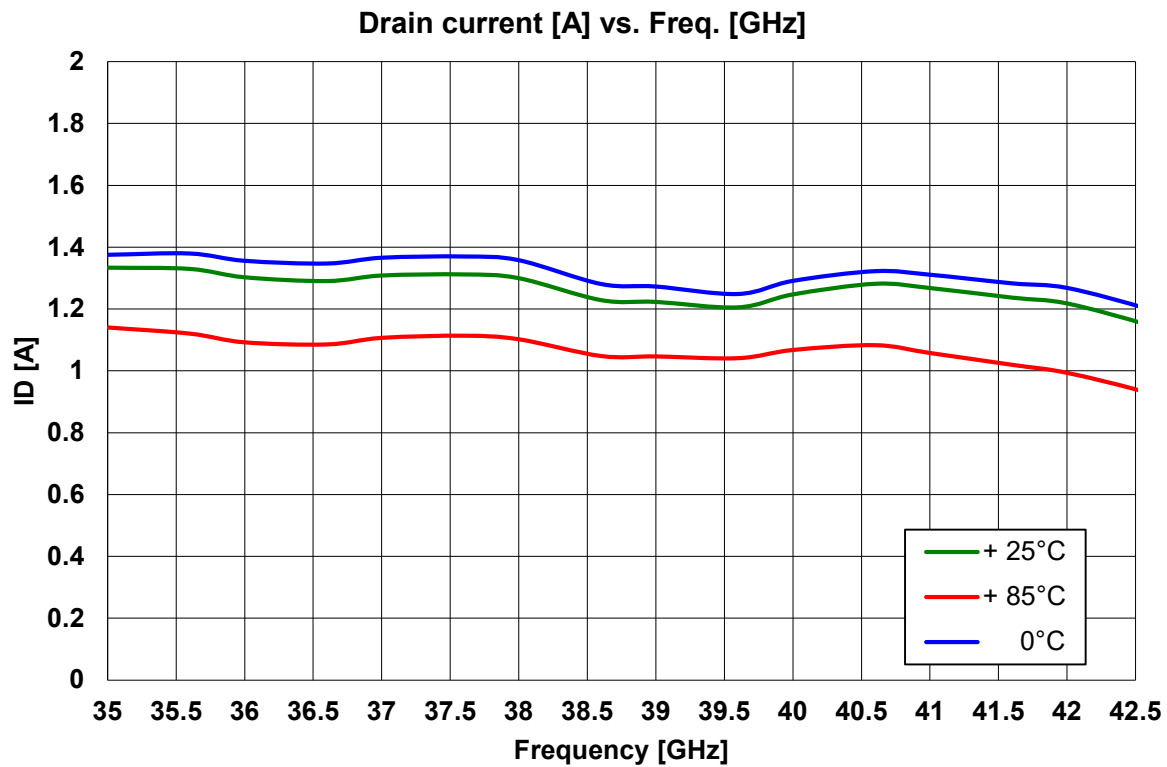
Typical on board Measurements: Large signal performance

T_{case} = 0°C/+25°C/85°C (QFN backside), V_d = +25V, I_{dq} = 300mA, Pin = 20dBm



Typical on board Measurements: Large signal performance

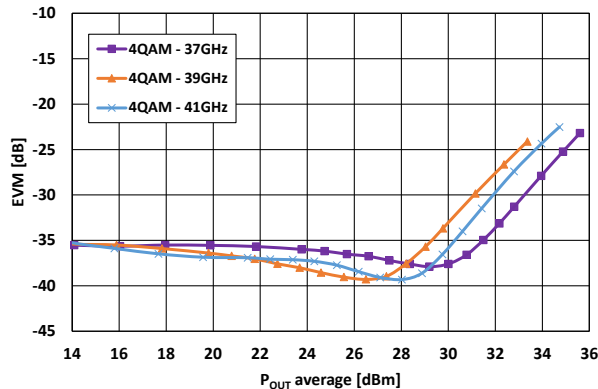
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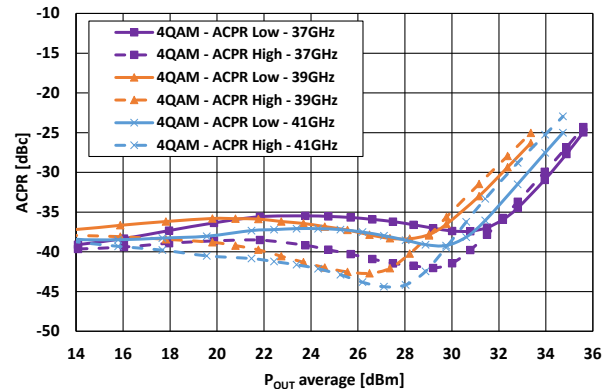
Typical Board Measurements: Linearity performance with modulated signals

T_{case} = +25°C, V_d = +25V, I_{dq} = 150mA, 4QAM (PAPR ~ 5.2dB) / 64QAM (PAPR ~ 7.3dB) / 256QAM (PAPR ~ 7.3dB), **SR = 50MSym/s**, Roll-Off = 0.2, f_{CARRIER} = 37/ 39/ 41GHz, Evaluation board decoupling : 10Ω+100pF / 10Ω+1nF/ 10Ω+1μF, QFN reference planes

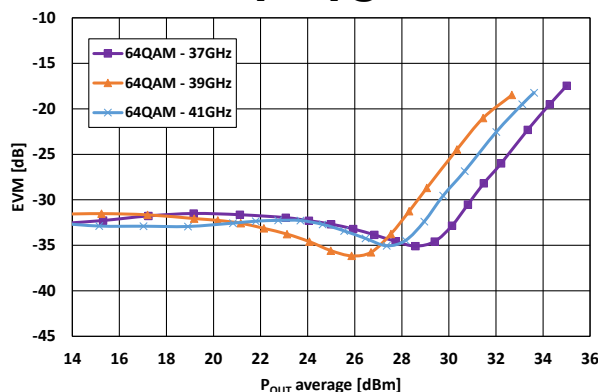
4QAM: EVM [dB] vs. Average Output Power [dBm] @ 25°C



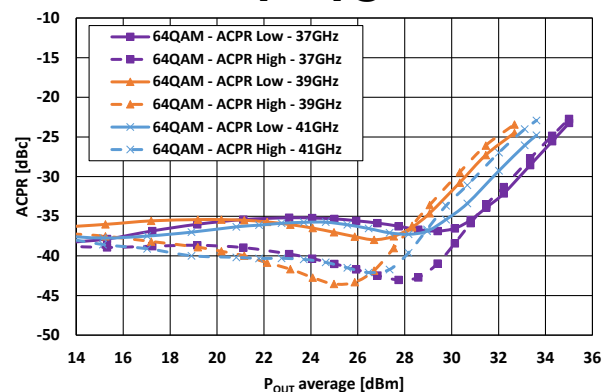
4QAM: ACPR [dBc] vs. Average Output Power [dBm] @ 25°C



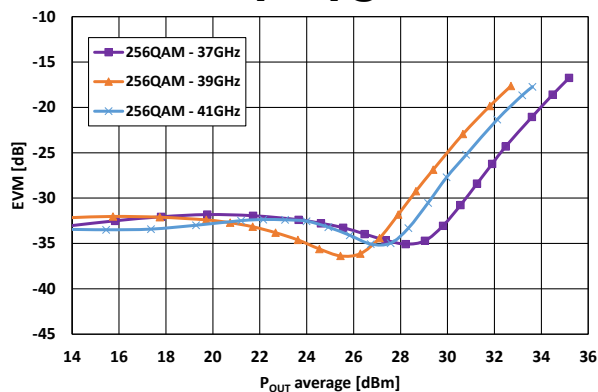
64QAM: EVM [dB] vs. Average Output Power [dBm] @ 25°C



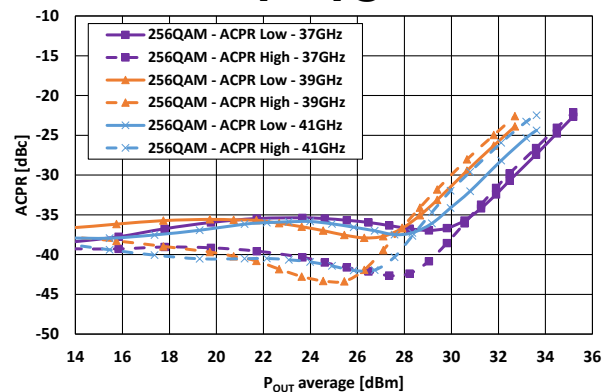
64QAM: ACPR [dBc] vs. Average Output Power [dBm] @ 25°C



256QAM: EVM [dB] vs. Average Output Power [dBm] @ 25°C



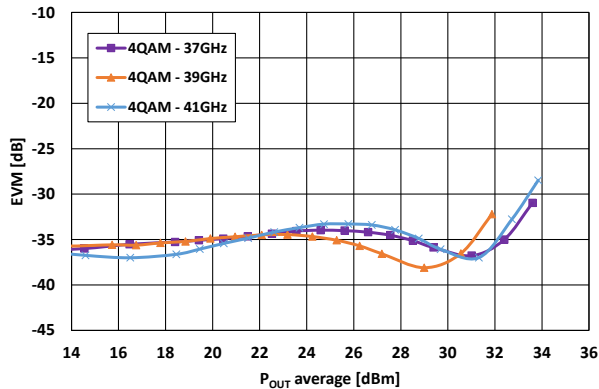
256QAM: ACPR [dBc] vs. Average Output Power [dBm] @ 25°C



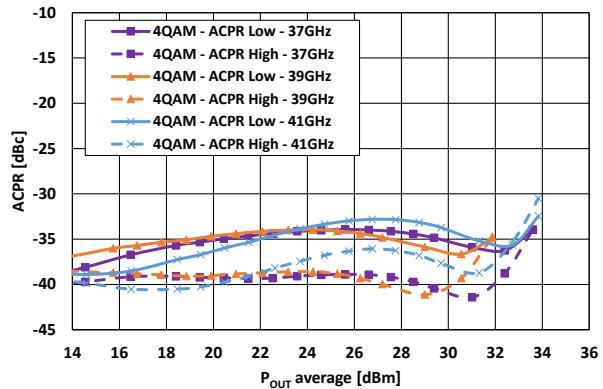
Typical Board Measurements: Linearity performance with modulated signals

T_{case} = +85°C, V_d = +25V, I_{dq} = 150mA, 4QAM (PAPR ~ 5.2dB) / 64QAM (PAPR ~ 7.3dB) / 256QAM (PAPR ~ 7.3dB), **SR = 50MSym/s**, Roll-Off = 0.2, f_{CARRIER} = 37/ 39/ 41GHz, Evaluation board decoupling : 10Ω+100pF / 10Ω+1nF/ 10Ω+1μF, QFN reference planes

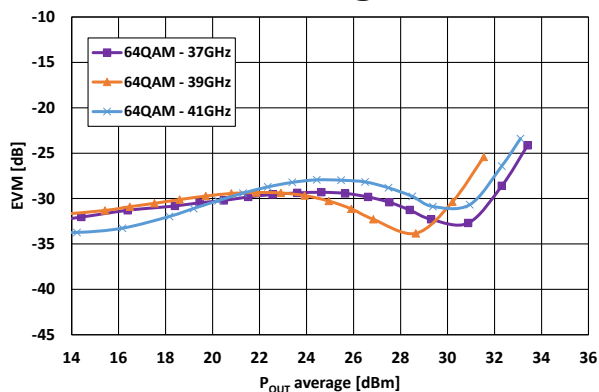
4QAM: EVM [dB] vs. Average Output Power [dBm] @ 85°C



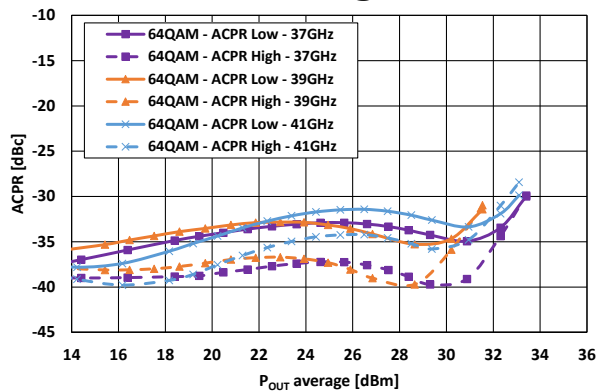
4QAM: ACPR [dBc] vs. Average Output Power [dBm] @ 85°C



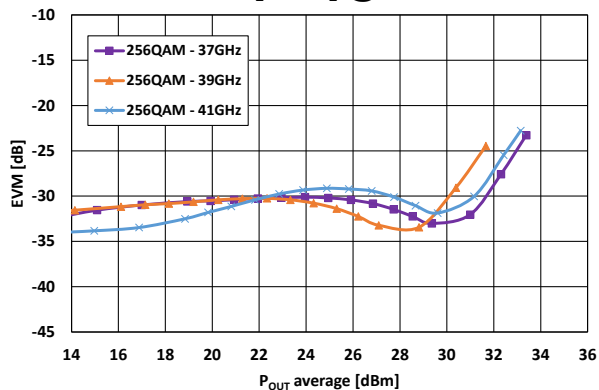
64QAM: EVM [dB] vs. Average Output Power [dBm] @ 85°C



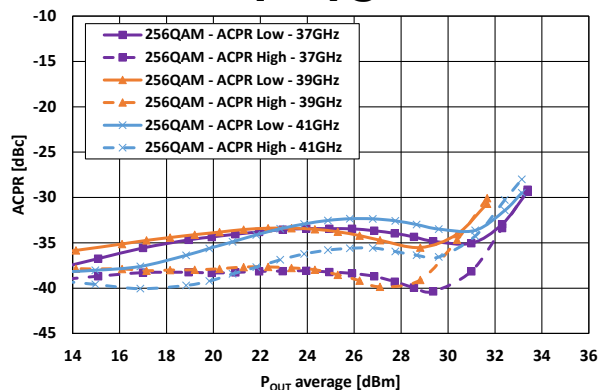
64QAM: ACPR [dBc] vs. Average Output Power [dBm] @ 85°C



256QAM: EVM [dB] vs. Average Output Power [dBm] @ 85°C



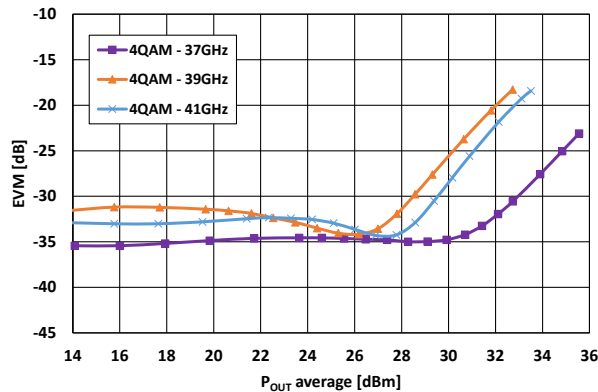
256QAM: ACPR [dBc] vs. Average Output Power [dBm] @ 85°C



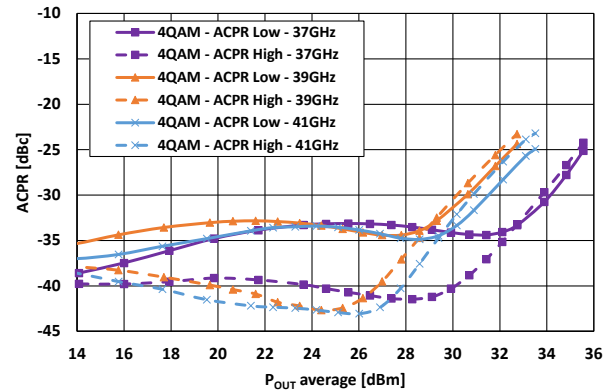
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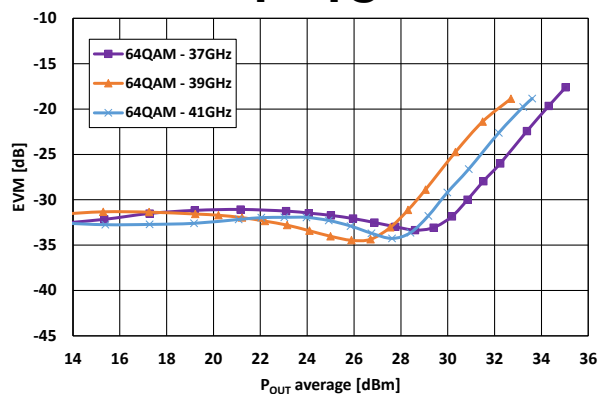
4QAM: EVM [dB] vs. Average Output Power [dBm] @ 25°C



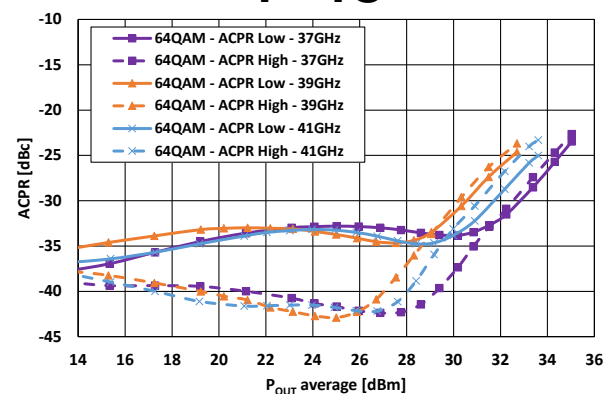
4QAM: ACPR [dBc] vs. Average Output Power [dBm] @ 25°C



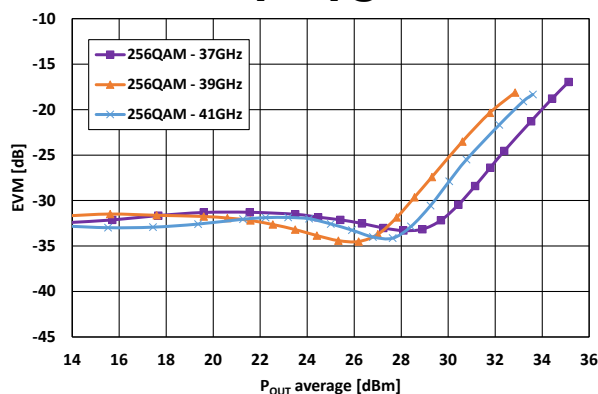
64QAM: EVM [dB] vs. Average Output Power [dBm] @ 25°C



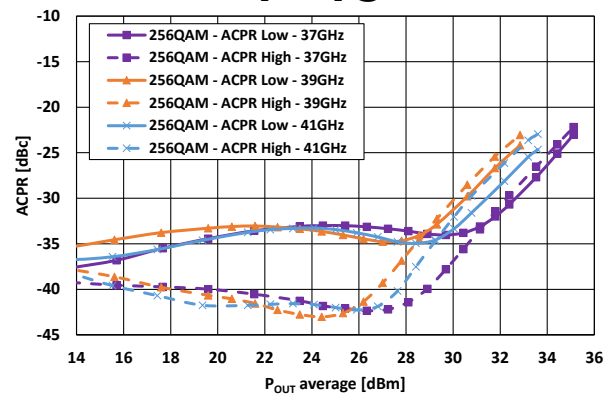
64QAM: ACPR [dBc] vs. Average Output Power [dBm] @ 25°C



256QAM: EVM [dB] vs. Average Output Power [dBm] @ 25°C



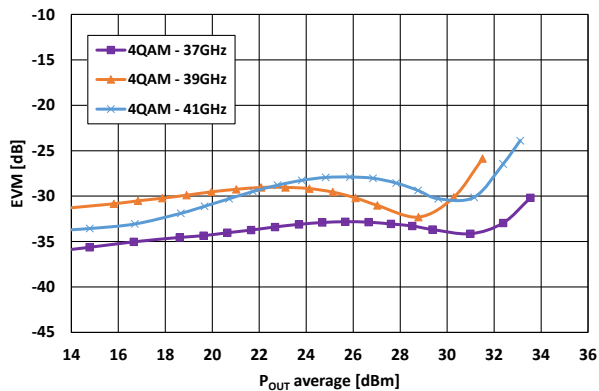
256QAM: ACPR [dBc] vs. Average Output Power [dBm] @ 25°C



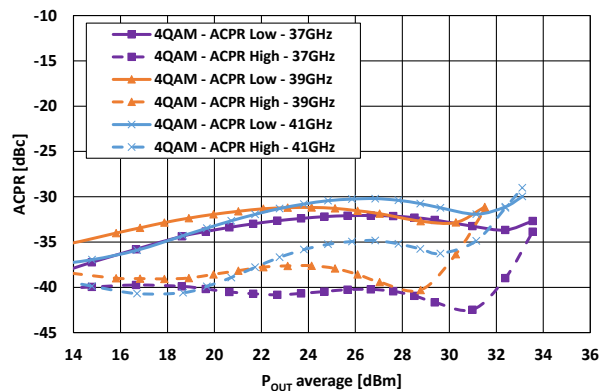
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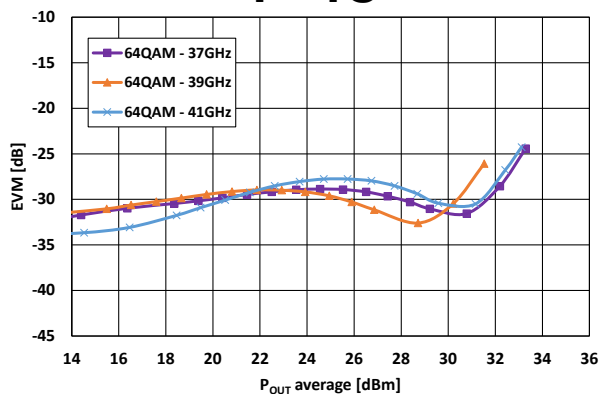
4QAM: EVM [dB] vs. Average Output Power [dBm] @ 85°C



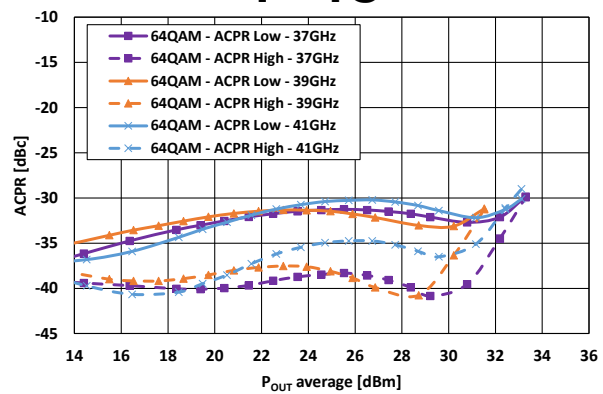
4QAM: ACPR [dBc] vs. Average Output Power [dBm] @ 85°C



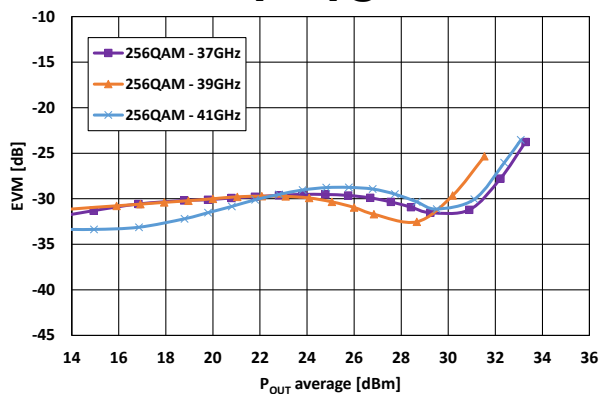
64QAM: EVM [dB] vs. Average Output Power [dBm] @ 85°C



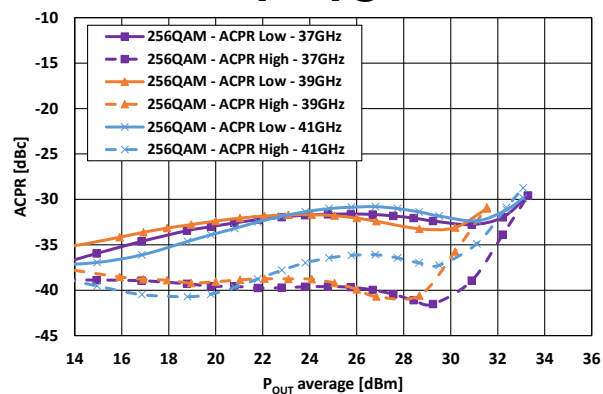
64QAM: ACPR [dBc] vs. Average Output Power [dBm] @ 85°C

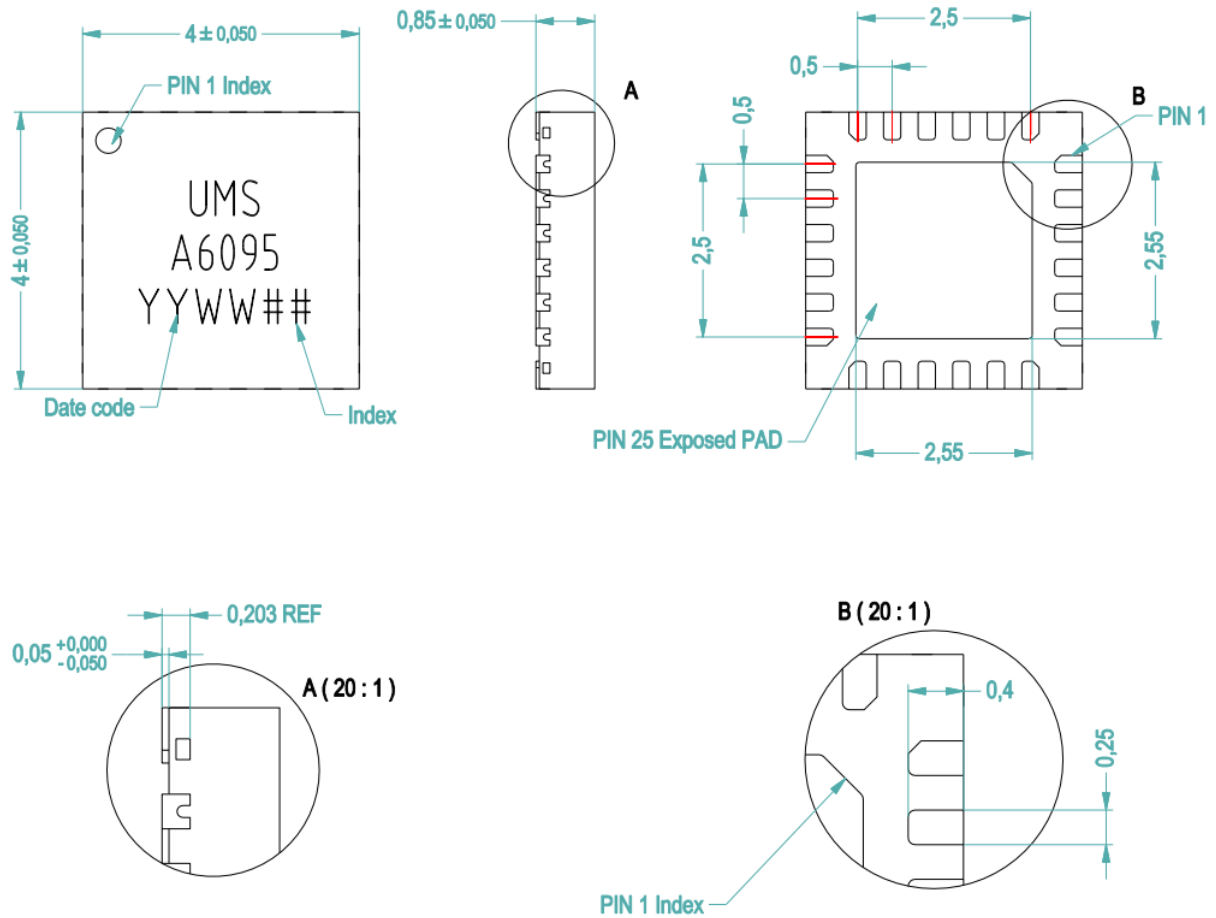


256QAM: EVM [dB] vs. Average Output Power [dBm] @ 85°C



256QAM: ACPR [dBc] vs. Average Output Power [dBm] @ 85°C



Package outline ⁽¹⁾**Package pinout**

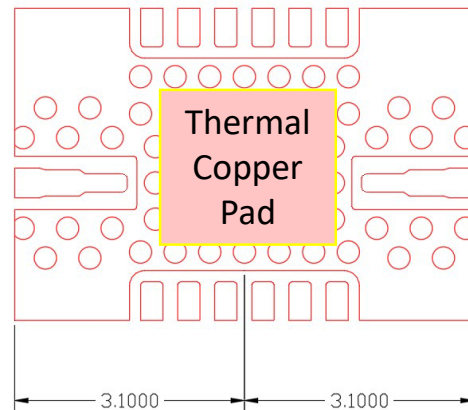
Ni-Pd-Au-Ag, Lead Free (Green)	1- VG12N	9- VG4S	17- NC
Units : mm	2- NC	10- VD12S	18- VD4N
From the standard : JEDEC MO-220	3- GND ⁽²⁾	11- VD3S	19- GND ⁽²⁾
(VGGD)	4- RF in	12- VD4S	20- VD3N
25- GND ⁽²⁾	5- GND ⁽²⁾	13- NC	21- VD12N
NC : Not Connected	6- NC	14- GND ⁽²⁾	22- VG4N
	7- VG12S	15- RF out	23- VG3N
	8- VG3S	16- GND ⁽²⁾	24- GND ⁽²⁾

⁽¹⁾ Refer to the application note AN0017 (<https://www.ums-rf.com>) for general consideration and recommendations for Molded Plastic QFN/DFN packages.

⁽²⁾ It is strongly recommended to ground all pins marked "GND" through the PCB board. Ensure that the PCB board is designed to provide the best possible ground to the package. See application note AN0017 for details.

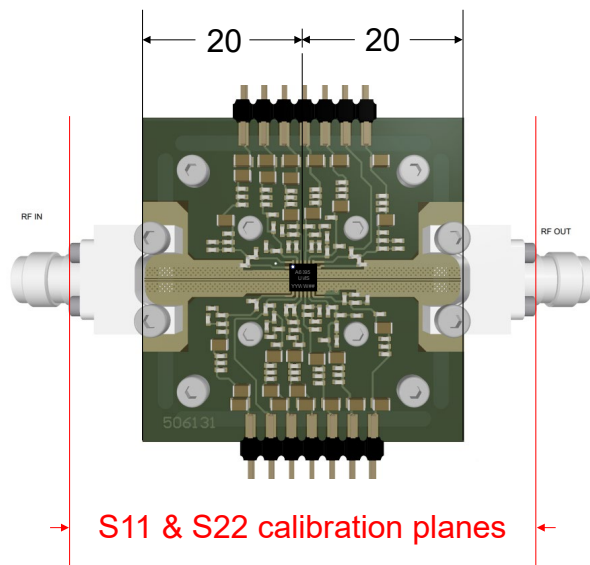
Definition of the QFN reference planes

Reference planes used for S21 and Power measurements are symmetrical from the central axis of the package (see drawing beside). Input and output reference planes are located at 3.1mm offset (input wise and output wise respectively) from this axis.



Definition of the evaluation board reference planes

Reference planes used for S11 and S22 measurements are symmetrical from the central axis of the package (see drawing beside also called calibration planes). Input and output reference planes are located at 20mm offset from the central axis. S11 and S22 measurements include this given PCB pattern, RF lines of the evaluation board and RF connectors.



ESD sensitivity

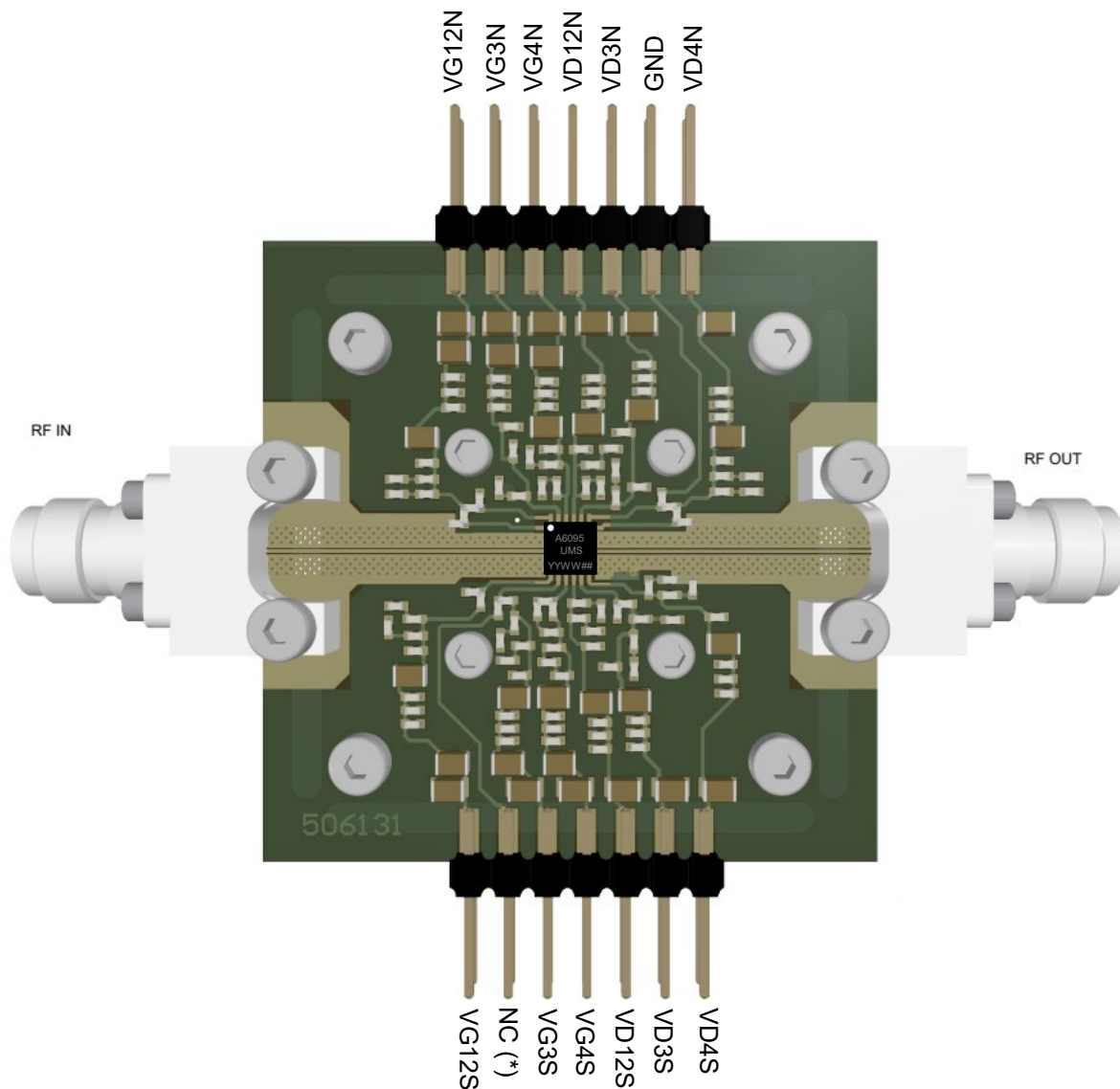
Parameter	Classification	Standard
Human Body Model (HBM)	1A	ANSI/ESDA/JEDEC - JS-001

Package Information

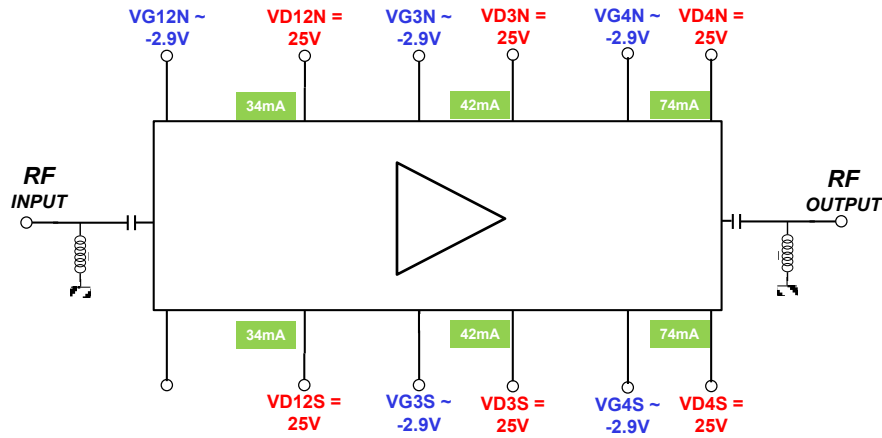
Parameter	Value
Package body material	RoHS-compliant
	Low stress Injection Molded Plastic
Lead finish	100% Ni-Pd-Au-Ag
MSL Rating	MSL3

Evaluation board

- Compatible with the proposed footprint.
- Based on typically MT77 / 10mils or equivalent.
- Using a micro-strip to coplanar transition to access the package.
- Recommended for the implementation of this product on a module board.
- Low frequency decoupling circuit of $10\Omega \pm 10\%$ resistor in series with $100\text{pF} \pm 5\%$ capacitor, $10\Omega \pm 10\%$ resistor in series with $1\text{nF} \pm 10\%$ capacitor and $10\Omega \pm 10\%$ resistor in series with $1\mu\text{F} \pm 10\%$ capacitor are recommended for each DC access.
- To ensure safe operation, all measurements must be performed using **shielded cables**, even for DC bias.



(*) Pins not connected.

DC Schematic

The DC pins do not include any decoupling capacitor in package, therefore it is mandatory to provide a good external DC decoupling (10 Ω $\pm$ 10% resistor in series with 100pF $\pm$ 5% capacitor, 10 Ω $\pm$ 10% resistor in series with 1nF $\pm$ 10% capacitor and 10 Ω $\pm$ 10% resistor in series with 1 μ F $\pm$ 10% capacitor) on the PCB as close as possible to the QFN package.

Recommended package footprint

Refer to the application note AN0017 available at <https://www.ums-rf.com> for package footprint recommendations.

SMD mounting procedure

For the mounting process standard techniques involving solder paste and a suitable reflow process can be used. For further details, see application note AN0017 at <https://www.ums-rf.com>.

Recommended environmental management

UMS products are compliant with the regulation in particular with the directives RoHS N°2011/65 and REACH N°1907/2006. More environmental data are available in the application note AN0019 also available at <https://www.ums-rf.com>.

Recommended ESD management

Refer to the application note AN0020 available at <https://www.ums-rf.com> for ESD sensitivity and handling recommendations for the UMS package products.

Description of Evaluation Board

Refer to the application note AN0031 available at <https://www.ums-rf.com> for the description of Evaluation Board for Packaged Die and recommendations for this UMS package product.

Ordering Information

QFN 4x4 package:

CHA6095-QKB/XY

Stick: XY = 20

Tape & reel: XY = 21

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